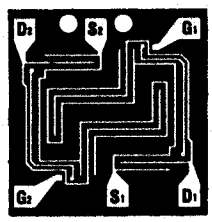
N-CHANNEL DUAL JUNCTION FET

Solitron Devices, Inc.

CHIP NUMBER

DMN113.3



.038" (0.965mm)

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Die Size:	38 x 38 (mils)
	0.965 x 0.965(mm)
	3.5 x 3.5(mils)
Pad Size:	0.089 x 0.089(mm)

CONTACT METALLIZATION

Top Contact: > 12,000 Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

a) the die be eutectically mounted with gold silicon preform 98/2%.

b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

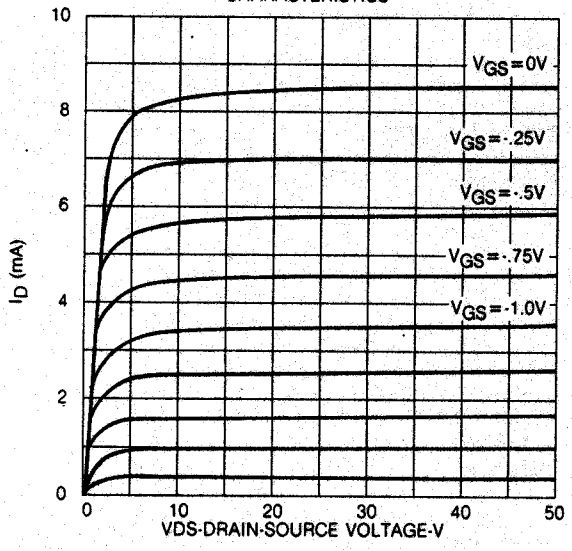
TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BV_{GSS}	-30	-50	-60	V	I_D = 1μA, V_{DS} = 0
I_{GSS}		30	200	pA	V_{DS} = 0, V_{GS} = -20V
I_{DSS}	1	6	15	mA	V_{DS} = 15V, V_{GS}, = 0
V_p	-.5	-2	-4	V	V_{DS} = 15V, I_D = 1nA
g_{fs}	1000		8000	μs	V_{DS} = 15V, V_{GS} = 0, f = 1KHz
y_{OS}			10	mho	V_{DS} = 15V, I_{DG} = 700μA
C_{iss}		16	18	pF	V_{DS} = 15V, V_{GS} = 0, f = 1MHz
C_{rss}		5	6	pF	V_{DS} = 15V, V_{GS} = 0, f = 1MHz

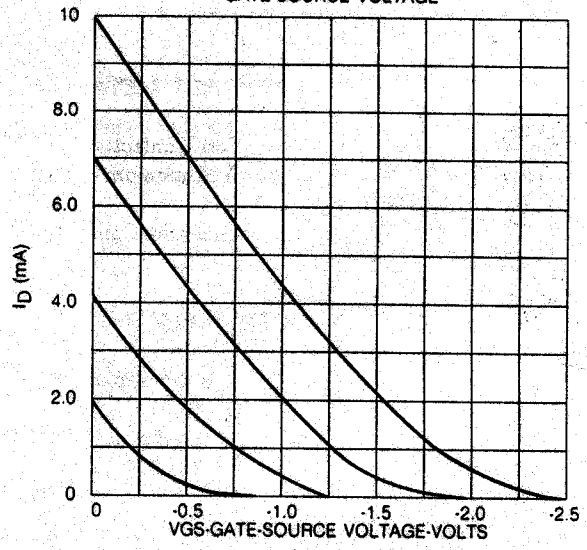
TYPICAL DEVICE TYPES: 2N3921 - 2N3922, 2N4084, 2N4085, SU2365 - SU2369, SU2080, SU2081

CHIP TYPE DMN113.3

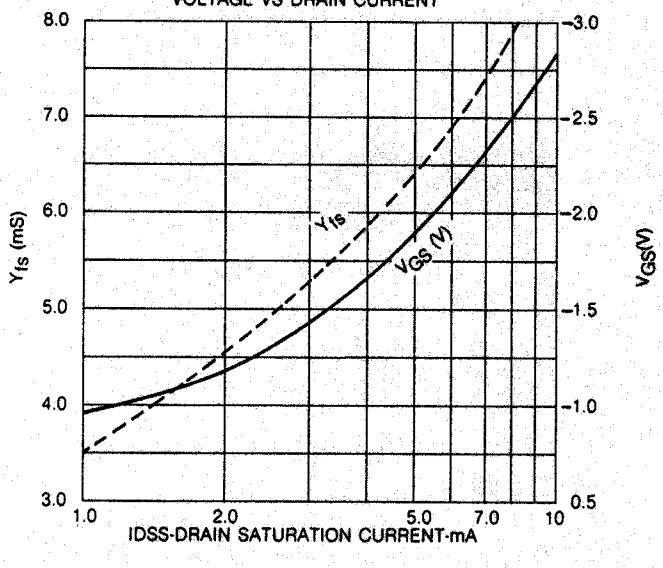
COMMON DRAIN-SOURCE CHARACTERISTICS



DRAIN CURRENT VS GATE-SOURCE VOLTAGE



TRANSADMITTANCE/CUT-OFF VOLTAGE VS DRAIN CURRENT



FORWARD TRANSADMITTANCE VS. DRAIN CURRENT